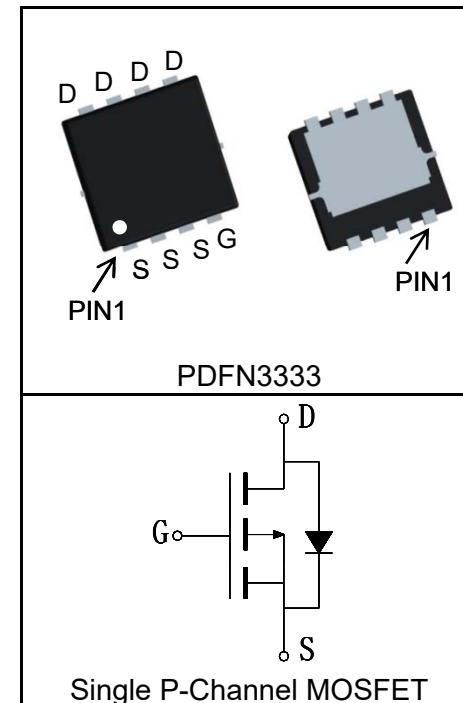


Features

- -20V/-65A,
- $R_{DS\ (ON)} = 5.8\text{m}\Omega\ (\text{Typ.}) @ V_{GS} = -4.5\text{V}$
- $R_{DS\ (ON)} = 8\text{m}\Omega\ (\text{Typ.}) @ V_{GS} = -2.5\text{V}$
- $R_{DS\ (ON)} = 12\text{m}\Omega\ (\text{Typ.}) @ V_{GS} = -1.8\text{V}$
- Low $R_{DS\ (ON)}$
- Super High Dense Cell Design
- Fast Switching Speed
- 100% avalanche tested

Pin Description



Applications

- Switching Application Systems



Halogen-Free

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$	-65
			A

Mounted on Large Heat Sink

$I_{DP}^{(1)}$	300 μs Pulse Drain Current Tested	$T_C = 25^\circ\text{C}$	-260	A
$I_D^{(2)}$	Continuous Drain Current@ $T_C(V_{GS} = -4.5\text{V})$	$T_C = 25^\circ\text{C}$	-65	A
		$T_C = 100^\circ\text{C}$	-41	
	Continuous Drain Current@ $T_A(V_{GS} = -4.5\text{V})^{(3)}$	$T_A = 25^\circ\text{C}$	-16	
		$T_A = 70^\circ\text{C}$	-13	
P_D	Maximum Power Dissipation@ T_C	$T_C = 25^\circ\text{C}$	42	W
		$T_C = 100^\circ\text{C}$	16	
	Maximum Power Dissipation@ T_A	$T_A = 25^\circ\text{C}$	3.5	
		$T_A = 70^\circ\text{C}$	2.3	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3	°C/W
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	35	°C/W
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	25	mJ

Electrical Characteristics ($T_C=25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS2306MA			Unit
			Min.	Typ.	Max.	

Static Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
		$T_J=125^\circ C$			-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-0.4	-0.6	-1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=-4.5V, I_{DS}=-20A$		5.8	8	mΩ
		$V_{GS}=-2.5V, I_{DS}=-12A$		8	11	mΩ
		$V_{GS}=-1.8V, I_{DS}=-10A$		12	15	mΩ

Diode Characteristics

$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=-20A, V_{GS}=0V$		-0.8	-1.2	V
t_{rr}	Reverse Recovery Time			80		ns
Q_{rr}	Reverse Recovery Charge	$I_{SD}=-20A, dI_{SD}/dt=100A/\mu s$		497		nC

Dynamic Characteristics⁽⁶⁾

R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		3.5		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-10V,$ Frequency=1.0MHz		6340		pF
C_{oss}	Output Capacitance			725		
C_{rss}	Reverse Transfer Capacitance			615		
$t_{d(ON)}$	Turn-on Delay Time			20		ns
t_r	Turn-on Rise Time	$V_{DD}=-10V, I_{DS}=-20A, V_{GS}=-4.5V, R_G=3\Omega$		54		
$t_{d(OFF)}$	Turn-off Delay Time			287		
t_f	Turn-off Fall Time			125		

Gate Charge Characteristics⁽⁶⁾

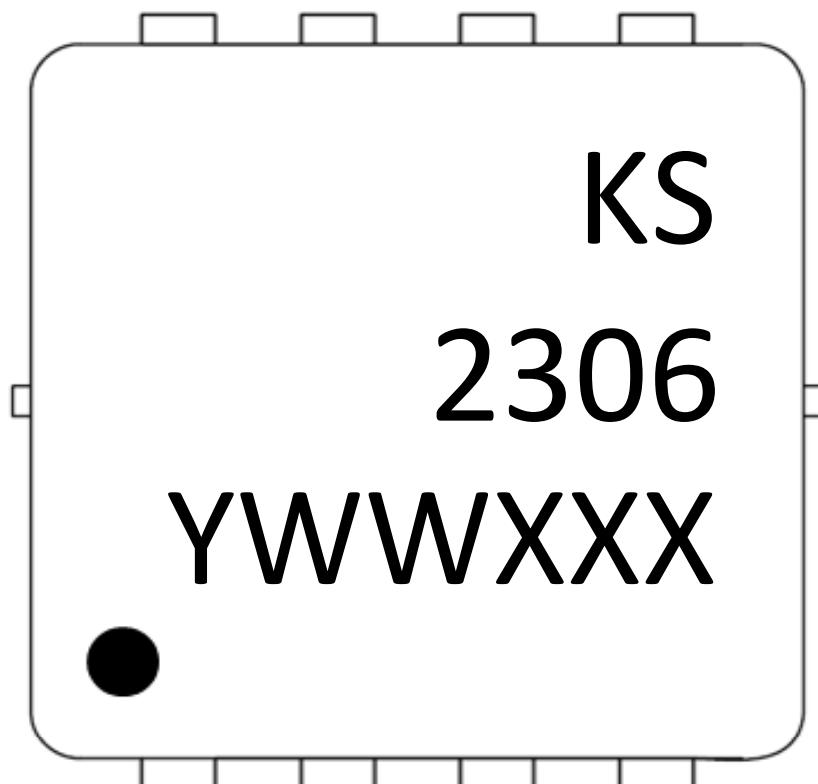
Q_g	Total Gate Charge	$V_{DS}=-10V, V_{GS}=-4.5V,$ $I_{DS}=-20A$		72		nC
Q_{gs}	Gate-Source Charge			11.2		
Q_{gd}	Gate-Drain Charge			20.4		

Notes:

- ①Pulse width limited by safe operating area.
- ②Calculated continuous current based on maximum allowable junction temperature.
- ③When mounted on 1 inch square copper board, $t \leq 10\text{sec}$.
- ④Limited by $T_{J\max}$, $I_{AS} = -10\text{A}$, $L=0.5\text{mH}$, $V_{DD} = -10\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.
- ⑤Pulse test; Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- ⑥Guaranteed by design, not subject to production testing.

Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS2306MA	PDFN3333	Tape&Reel	5000	13"	12mm

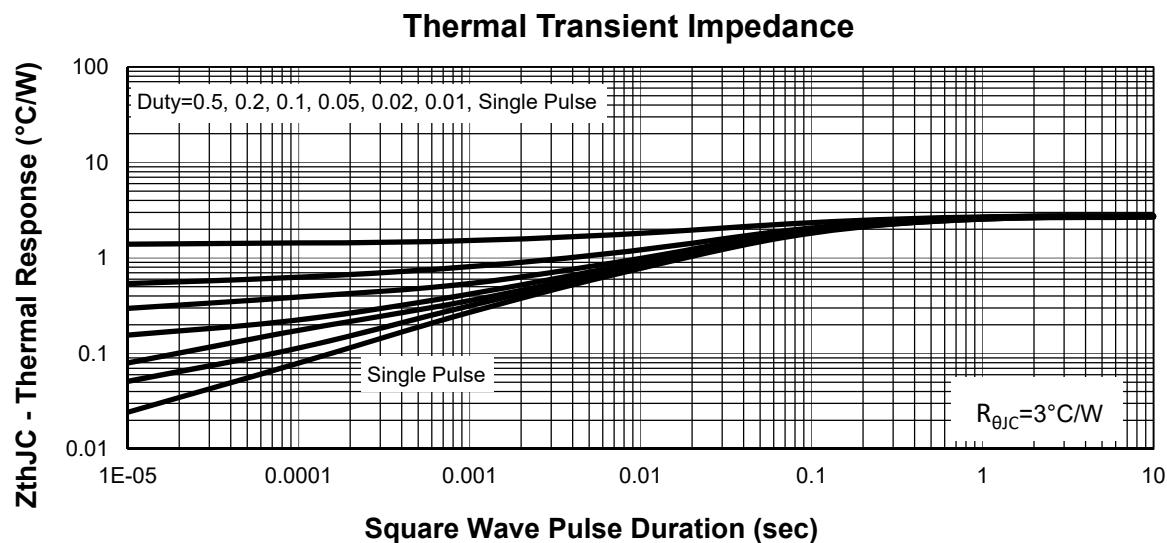
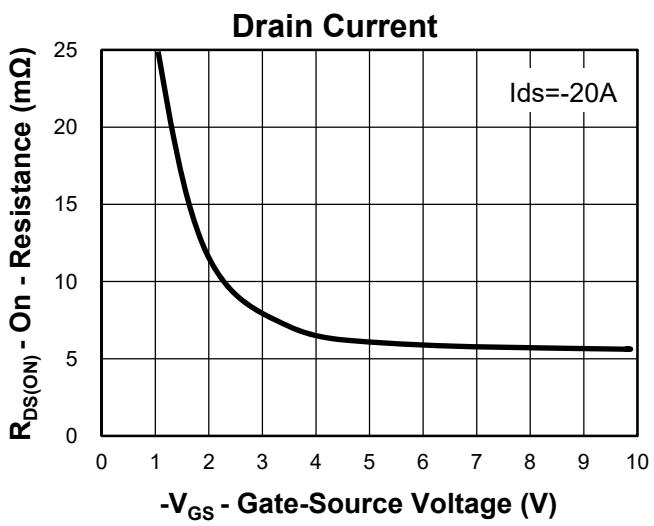
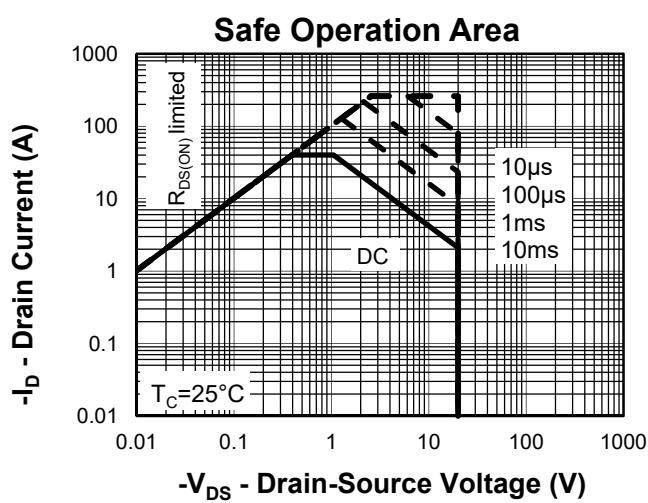
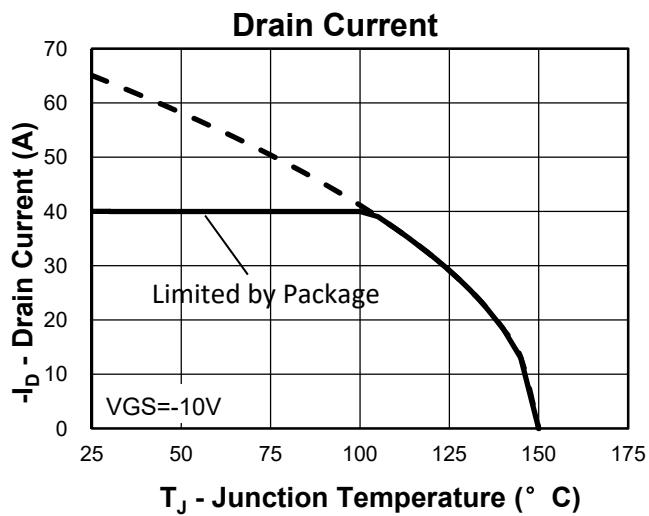
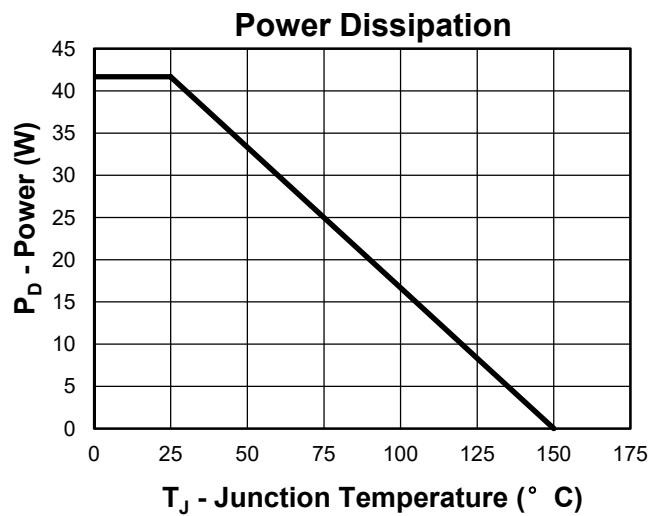


Y =Year, 2017-A, 2018-B,etc.

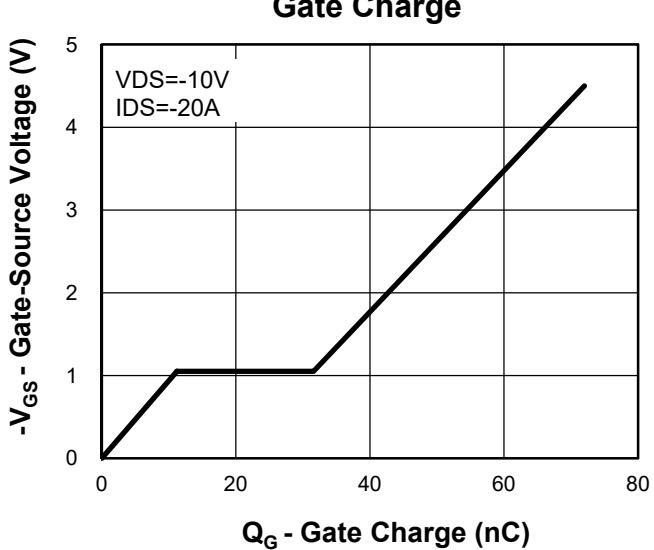
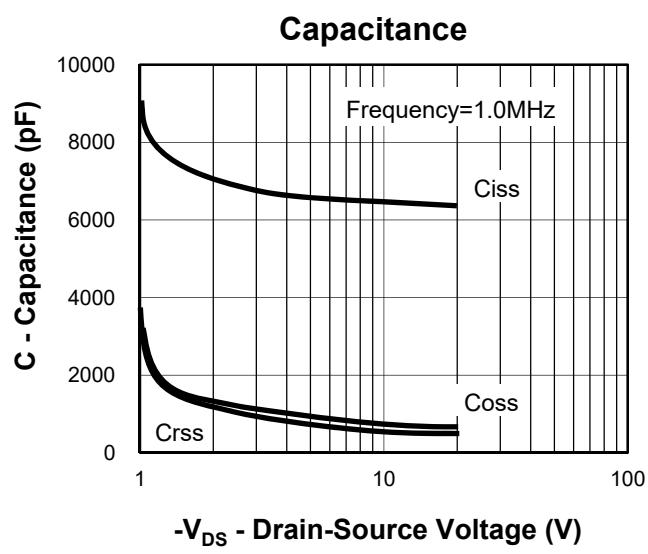
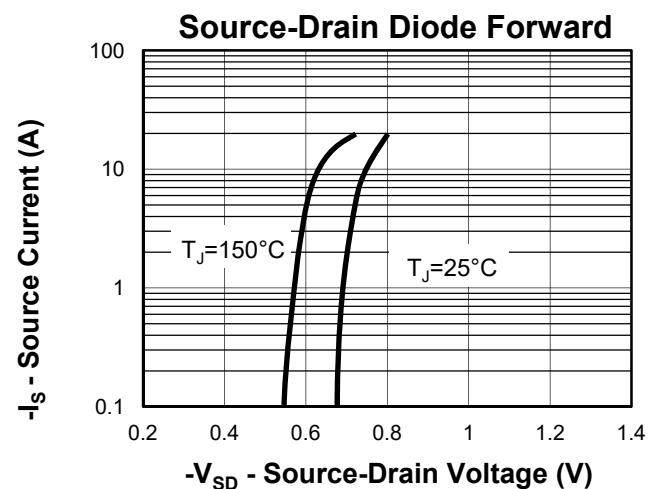
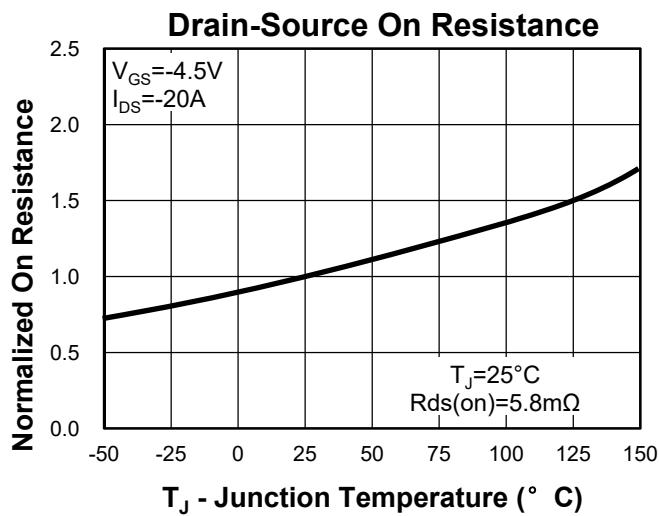
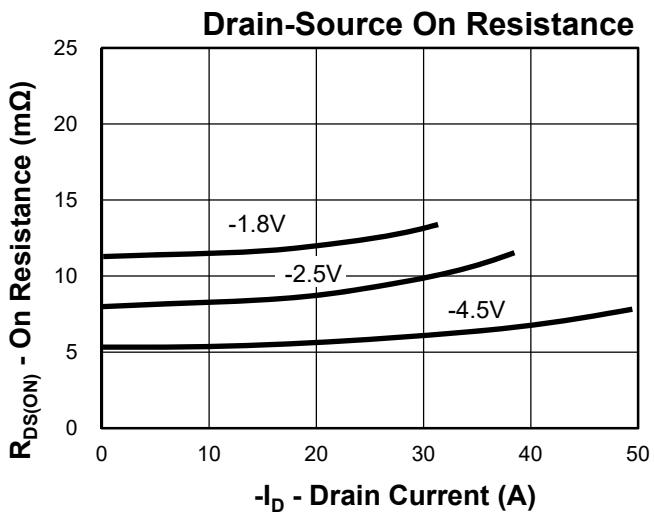
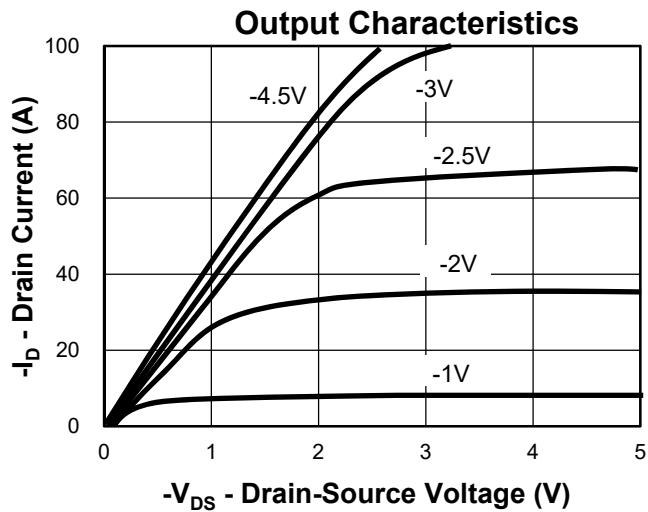
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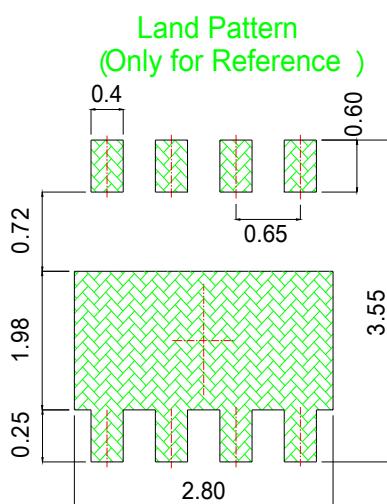
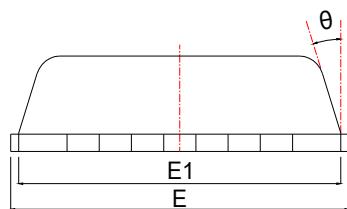
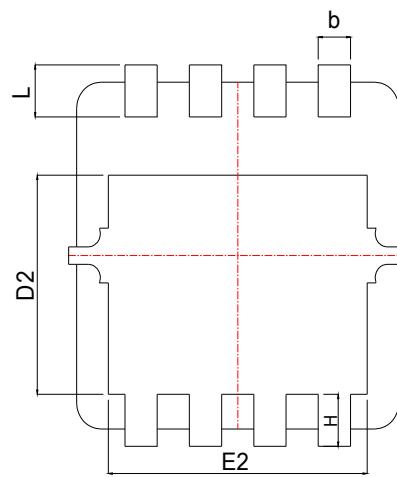
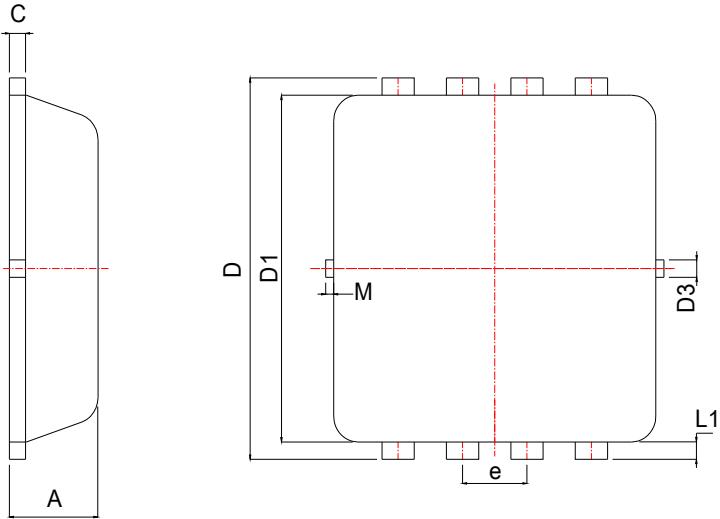
XXX =Lot number.

Typical Characteristics



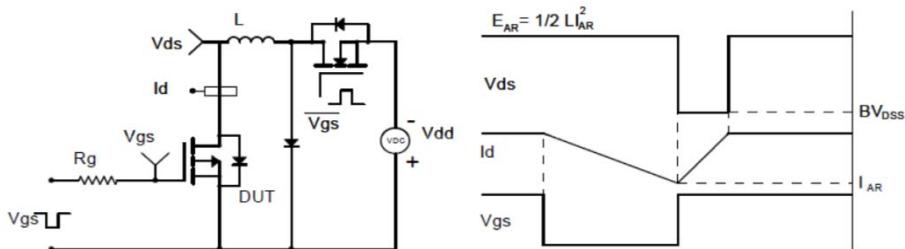
Typical Characteristics



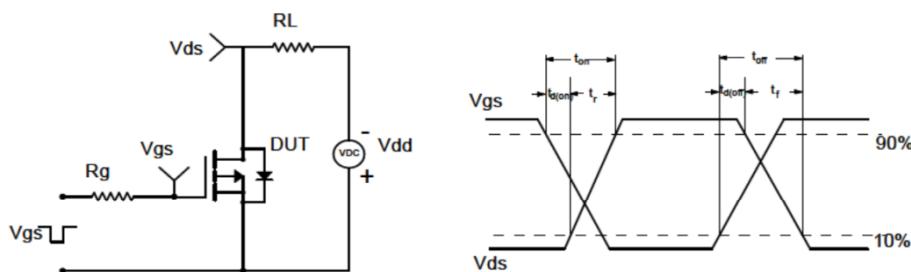
Package Information
PDFN3333


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.67	0.78	0.88	0.026	0.031	0.035	E1	3.05	3.15	3.25	0.120	0.124	0.128
b	0.25	0.30	0.35	0.010	0.012	0.014	E2	2.25	2.45	2.65	0.089	0.096	0.104
c	0.10	0.15	0.25	0.004	0.006	0.010	e	0.65BSC			0.026BSC		
D	3.15	3.35	3.55	0.124	0.132	0.140	H	0.30	0.40	0.50	0.012	0.016	0.020
D1	3.00	3.10	3.20	0.118	0.122	0.126	L	0.30	0.40	0.50	0.012	0.016	0.020
D2	1.53	1.73	1.93	0.060	0.068	0.076	L1	*	0.13	*	*	0.005	*
D3	*	0.13	*	*	0.005	*	θ	*	10°	12°	*	10°	12°
E	3.10	3.30	3.50	0.122	0.130	0.138	M	*	*	0.15	*	*	0.006

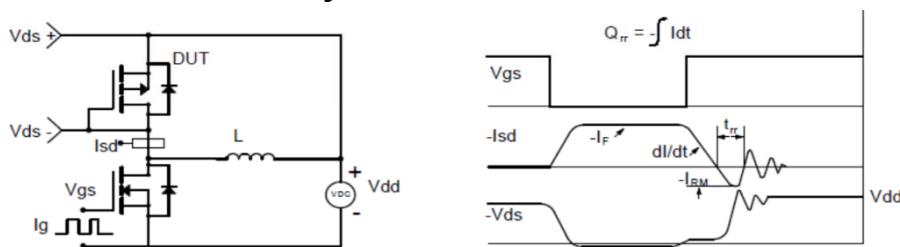
Avalanche Test Circuit and Waveforms



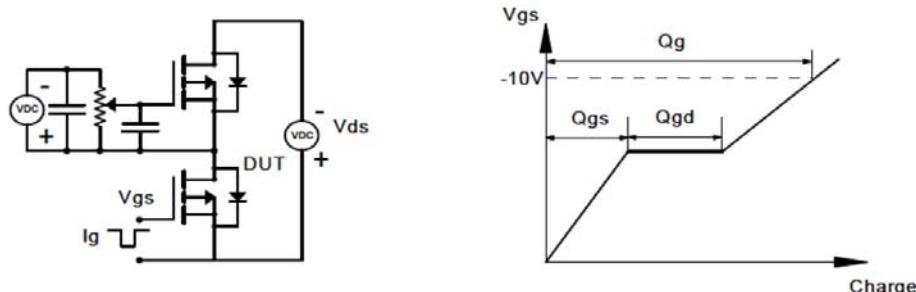
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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